

CLAIMS

1. A light emitting device, being characterized by forming a semiconductor layer on an uneven surface of an uneven substrate.

5 2. The light emitting device as set forth in Claim 1, wherein the uneven substrate and the semiconductor layer comprise $\text{Al}_x\text{Ga}_y\text{In}_{1-x-y}\text{N}$ ($0 \leq x$, $0 \leq y$, $x+y \leq 1$).

3. The light emitting device as set forth in Claim 1 or 2, wherein each of the planes forming the uneven surface of the uneven substrate has at least
10 one plane index selected from among (11-2L) and (1-10L), wherein L represents an integer from 1 to 4.

4. The light emitting device as set forth in Claim 1 or 2, wherein the angle formed between each of the planes forming the uneven surface of the uneven substrate and the base plane is from 35° to 80°.